N- and P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	12	0.235 @ V_{GS} = 4.5 V	1.3
		0.280 @ V_{GS} = 2.5 V	1.2
		0.340 @ V_{GS} = 1.8 V	1.0
P-Channel	-12	0.535 @ V_{GS} = -4.5 V	-0.86
		0.880 @ V_{GS} = -2.5 V	-0.67
		1.26 @ V_{GS} = -1.8 V	-0.56

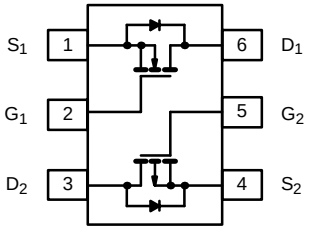
FEATURES

- TrenchFET® Power MOSFETs
- Thermally Enhanced SC-70 Package
- Fast Switching to Minimize Gate and Switching Losses

APPLICATIONS

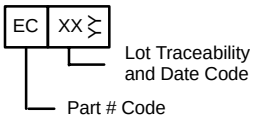
- Baseband DC/DC Converter Switch for Portable Electronics

SOT-363
SC-70 (6-LEADS)



Top View

Marking Code



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	N-Channel		P-Channel		Unit
			5 secs	Steady State	5 secs	Steady State	
Drain-Source Voltage		V_{DS}	12		-12		V
Gate-Source Voltage		V_{GS}	±8				
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	1.3	1.2	- 0.86	-0.77	A
	T_A = 85°C		0.9	0.8	-0.62	-0.55	
Pulsed Drain Current		I_{DM}	3		-2		
Continuous Source Current (Diode Conduction)[a]		I_S	0.5	0.39	-0.5	-0.39	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	0.6	0.47	0.6	0.47	W
	T_A = 85°C		0.3	0.25	0.3	0.25	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150				°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 5 sec	R_{thJA}	170	210	°C/W
	Steady State		220	265	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	105	125	

Notes
a. Surface Mounted on 1” x 1” FR4 Board.

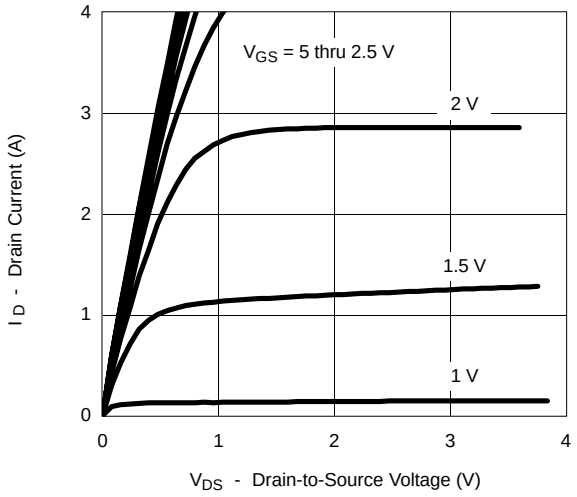
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Static							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 100 μA	N-Ch	0.45		1	V
		V_{DS} = V_{GS}, I_D = -100 μA	P-Ch	-0.45		1	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V	N-Ch			±100	nA
			P-Ch			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 9.6 V, V_{GS} = 0 V	N-Ch			1	μA
		V_{DS} = -9.6 V, V_{GS} = 0 V	P-Ch			-1	
		V_{DS} = 9.6 V, V_{GS} = 0 V, T_J = 85°C	N-Ch			5	
		V_{DS} = -9.6 V, V_{GS} = 0 V, T_J = 85°C	P-Ch			-5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 4.5 V	N-Ch	3			A
		V_{DS} ≤ -5 V, V_{GS} = -4.5 V	P-Ch	-2			
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 1.2 A	N-Ch		0.195	0.235	Ω
		V_{GS} = -4.5 V, I_D = -0.77 A	P-Ch		0.445	0.535	
		V_{GS} = 2.5 V, I_D = 1.0 A	N-Ch		0.230	0.280	
		V_{GS} = -2.5 V, I_D = -0.6 A	P-Ch		0.735	0.880	
		V_{GS} = 1.8 V, I_D = 0.2 A	N-Ch		0.284	0.340	
		V_{GS} = -1.8 V, I_D = -0.2 A	P-Ch		1.05	1.26	
Forward Transconductance[a]	g_{fs}	V_{DS} = 5 V, I_D = 1.2 A	N-Ch		0.8		S
		V_{DS} = -5 V, I_D = -0.77 A	P-Ch		1.2		
Diode Forward Voltage[a]	V_{SD}	I_S = 0.39 A, V_{GS} = 0 V	N-Ch		0.8	1.2	V
		I_S = -0.39 A, V_{GS} = 0 V	P-Ch		-0.8	-1.2	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 6 V, V_{GS} = 4.5 V, I_D = 1.2 A P-Channel V_{DS} = -6 V, V_{GS} = -4.5 V, I_D = -0.1 A	N-Ch		0.8	1.2	nC
			P-Ch		1.1	1.8	
Gate-Source Charge	Q_{gs}		N-Ch		0.15		
			P-Ch		0.3		
Gate-Drain Charge	Q_{gd}		N-Ch		0.20		
			P-Ch		0.25		
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 6 V, R_L = 12 Ω I_D ≅ 0.5 A, V_{GEN} = 4.5 V, R_G = 6 Ω P-Channel V_{DD} = -6 V, R_L = 12 Ω I_D ≅ -0.5 A, V_{GEN} = -4.5 V, R_G = 6 Ω	N-Ch		15	25	ns
			P-Ch		17	25	
Rise Time	t_r		N-Ch		25	40	
			P-Ch		30	45	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		25	40	
			P-Ch		15	25	
Fall Time	t_f		N-Ch		10	15	
			P-Ch		10	15	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 0.39 A, di/dt = 100 A/μs	N-Ch		20	40	
		I_F = -0.39 A, di/dt = 100 A/μs	P-Ch		25	40	

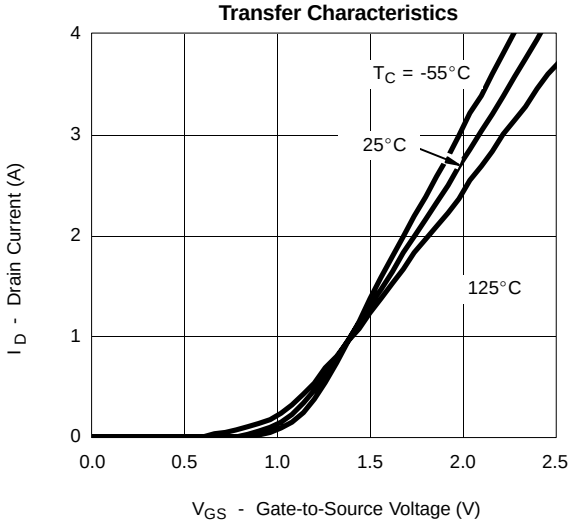
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

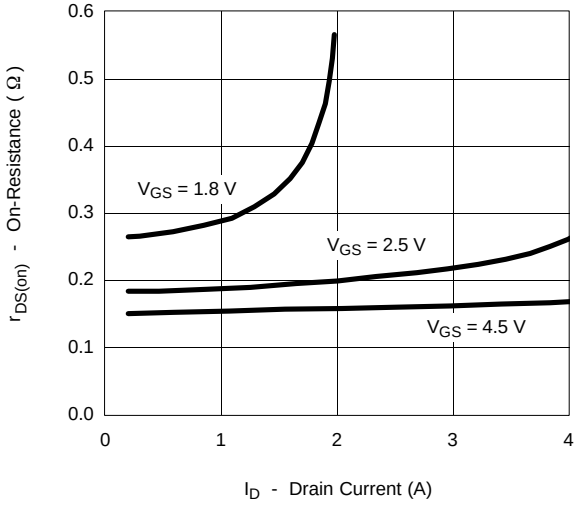
Output Characteristics



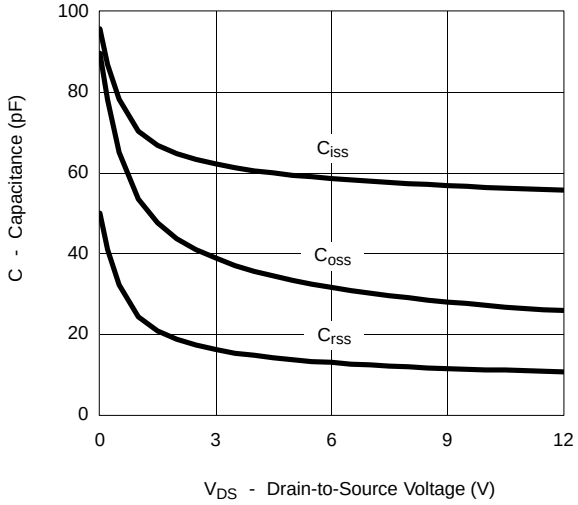
Transfer Characteristics



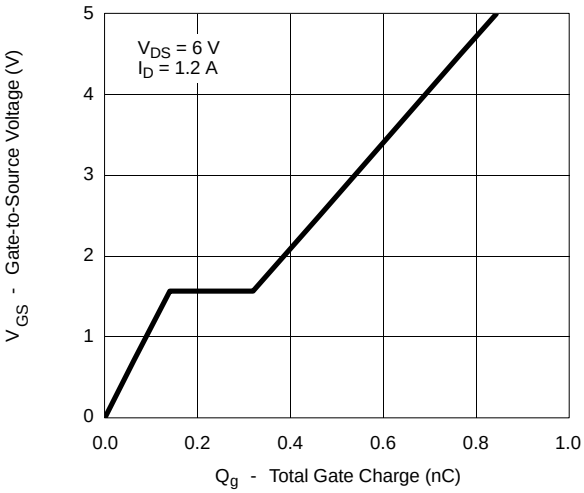
On-Resistance vs. Drain Current



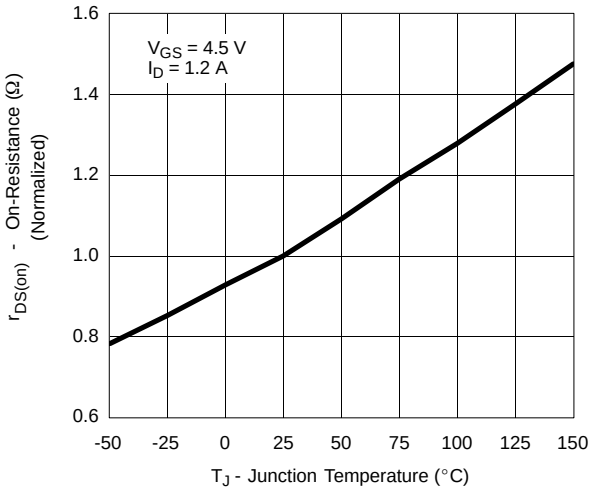
Capacitance



Gate Charge

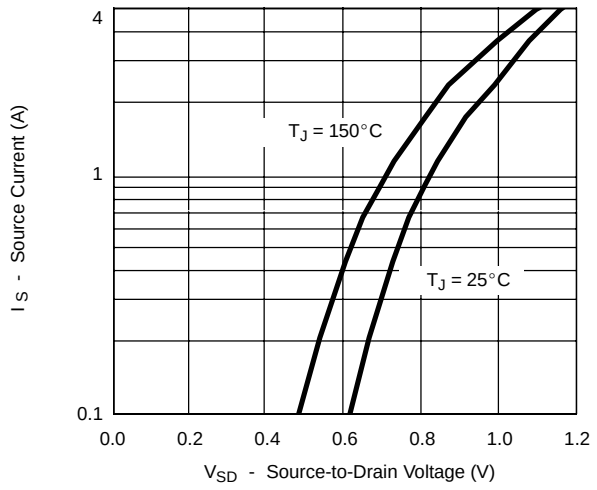


On-Resistance vs. Junction Temperature

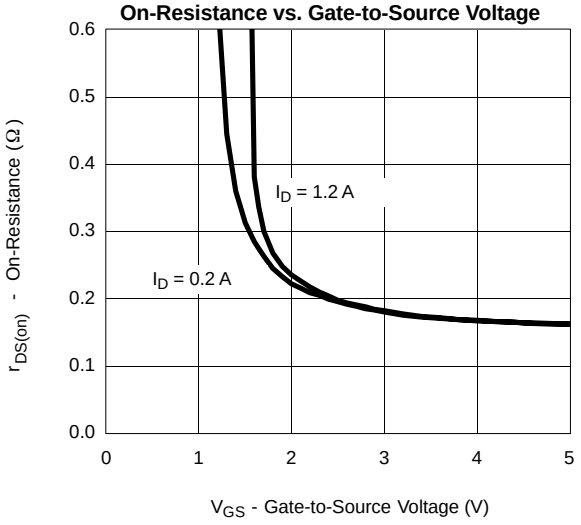


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

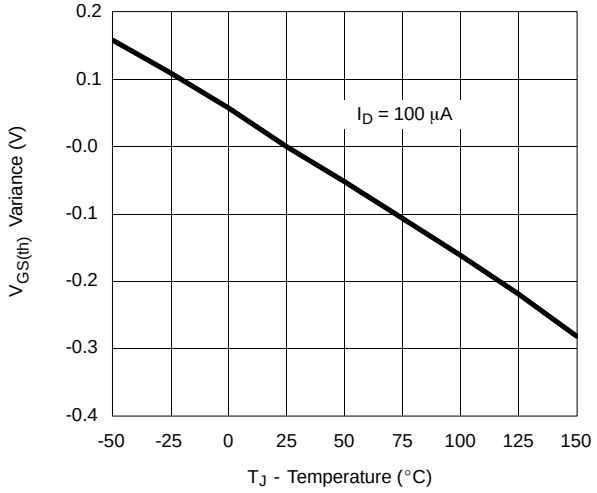
Source-Drain Diode Forward Voltage



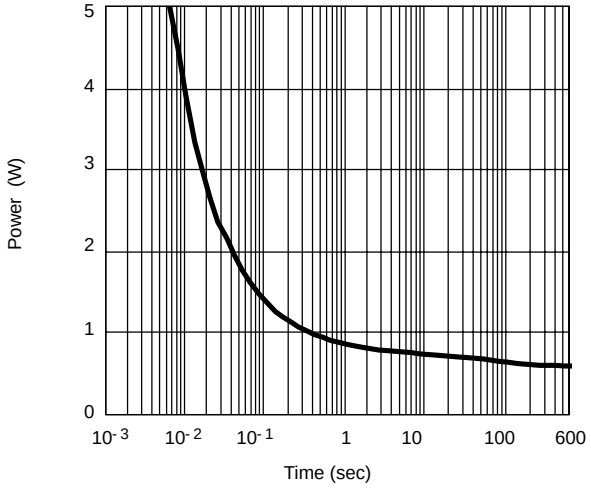
On-Resistance vs. Gate-to-Source Voltage



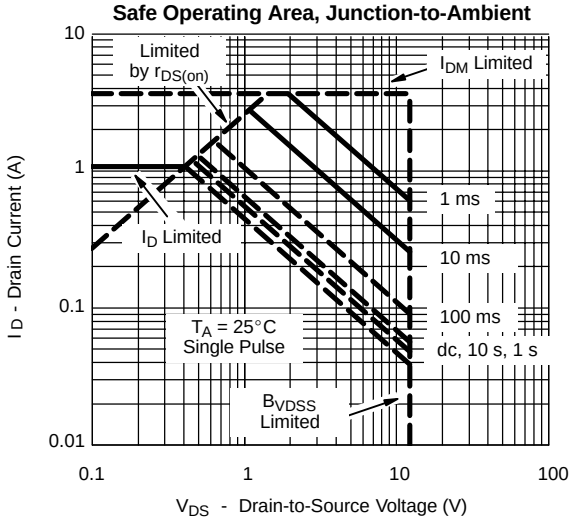
Threshold Voltage



Single Pulse Power

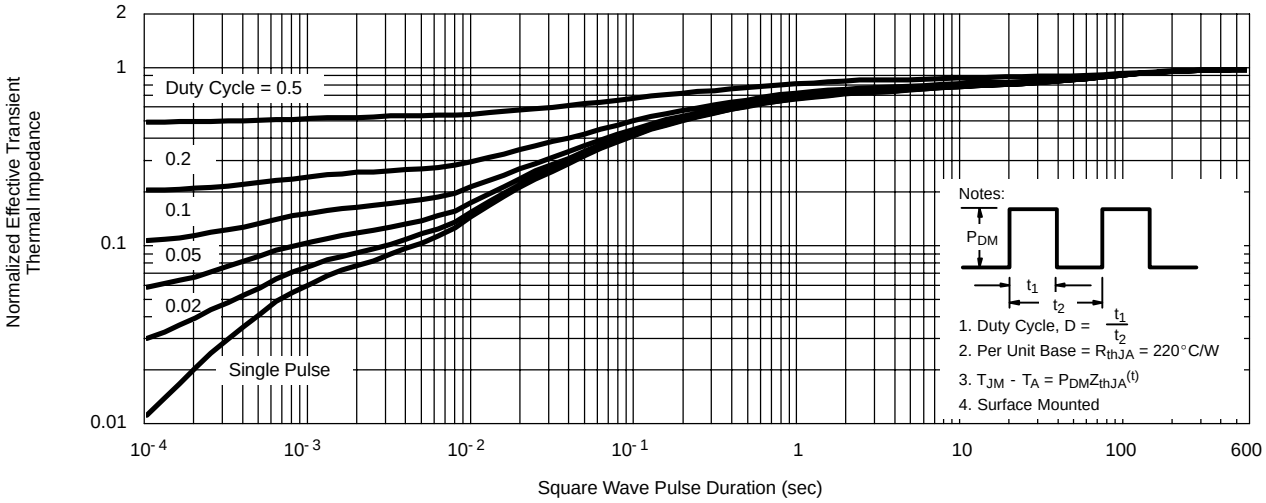


Safe Operating Area, Junction-to-Ambient

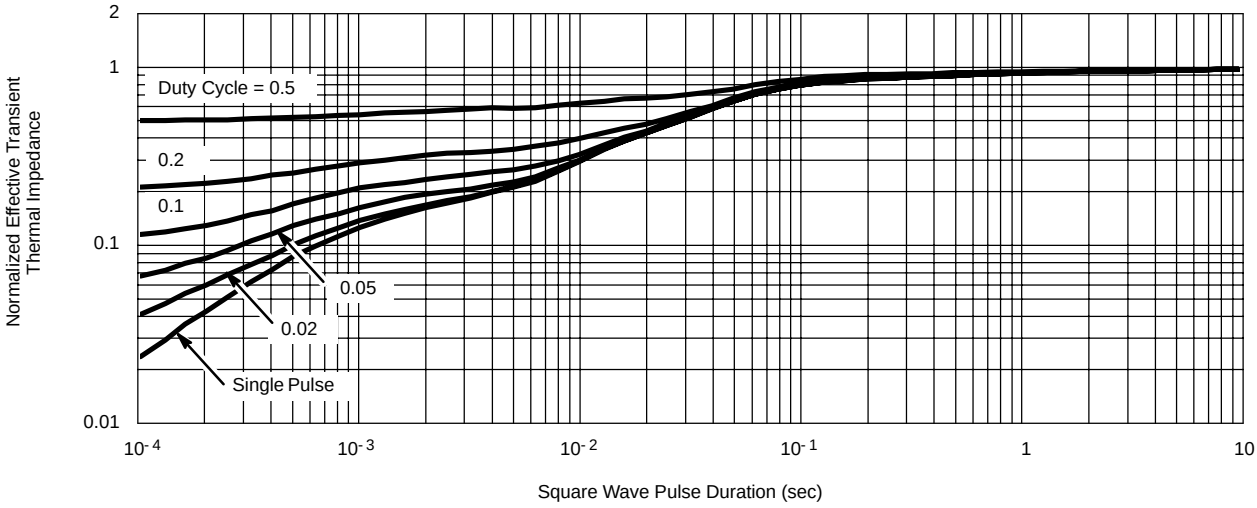


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

Normalized Thermal Transient Impedance, Junction-to-Ambient

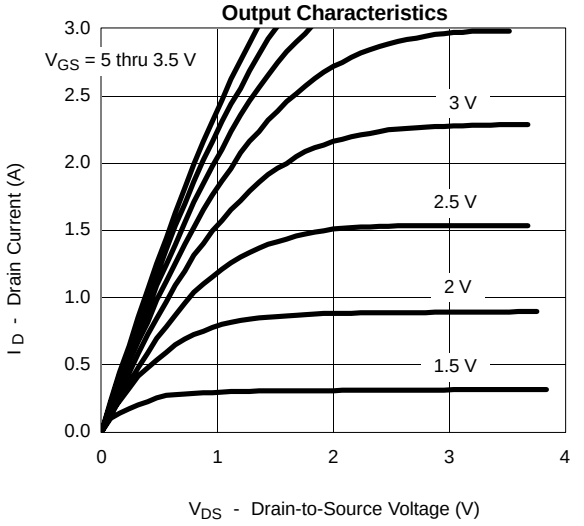


Normalized Thermal Transient Impedance, Junction-to-Foot

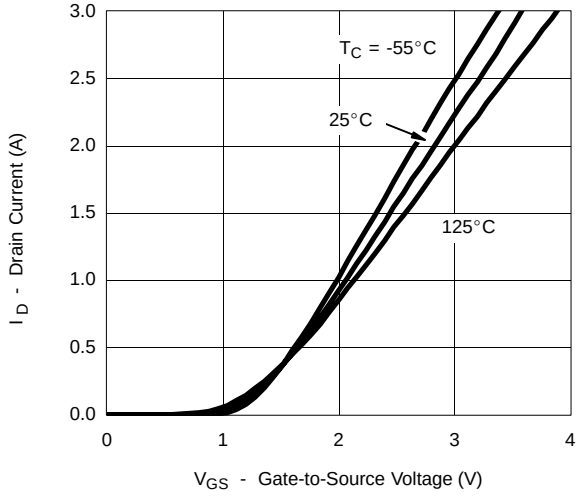


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

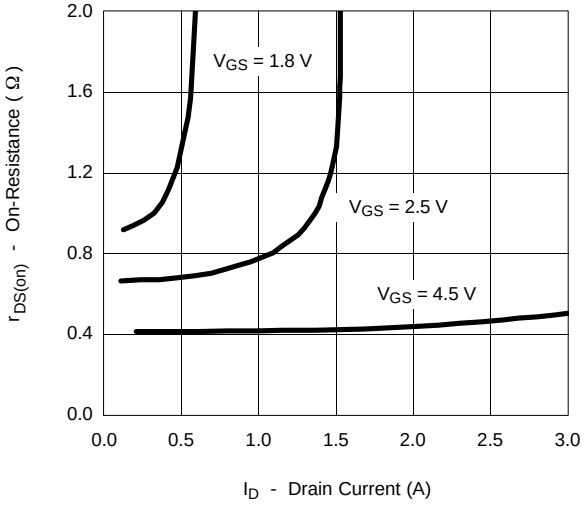
Output Characteristics



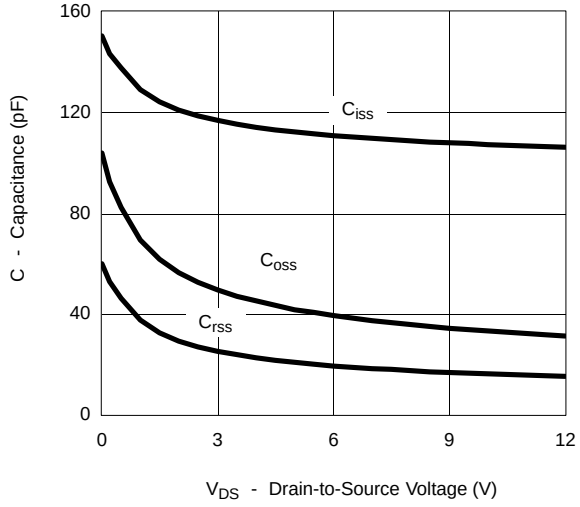
Transfer Characteristics



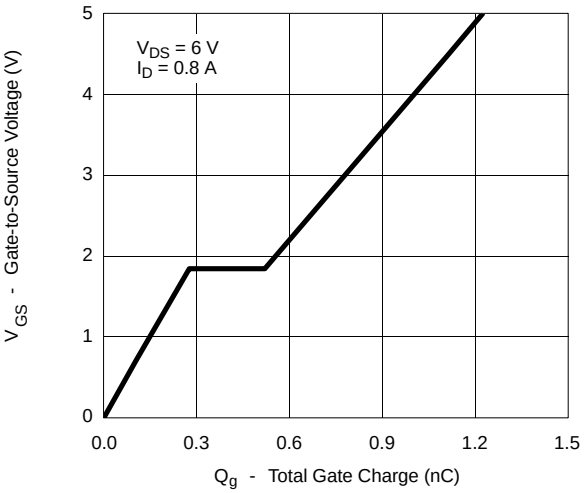
On-Resistance vs. Drain Current



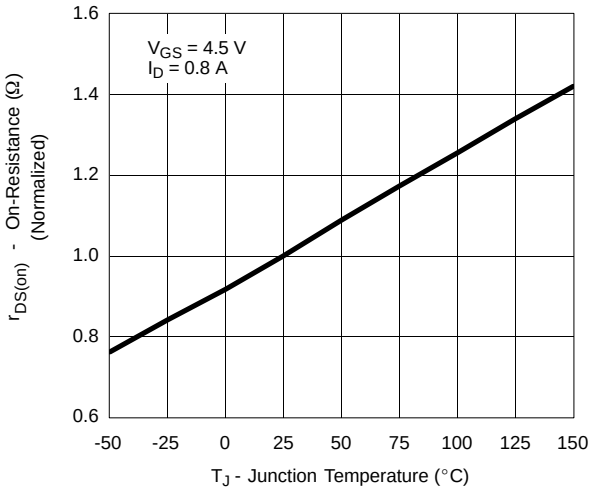
Capacitance



Gate Charge

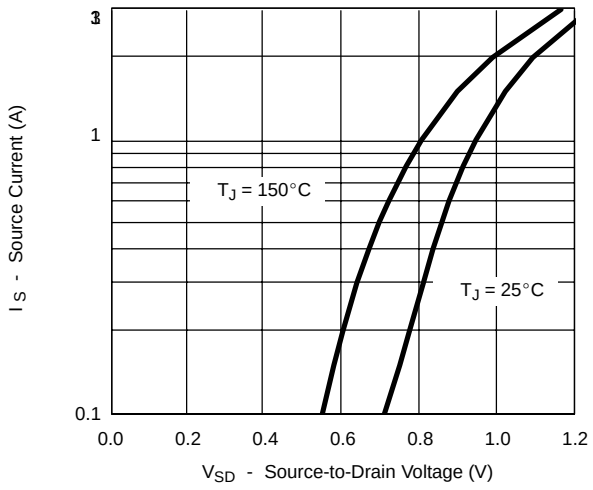


On-Resistance vs. Junction Temperature

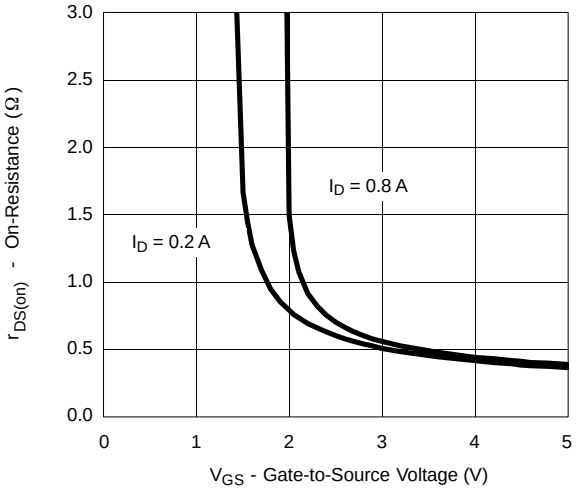


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

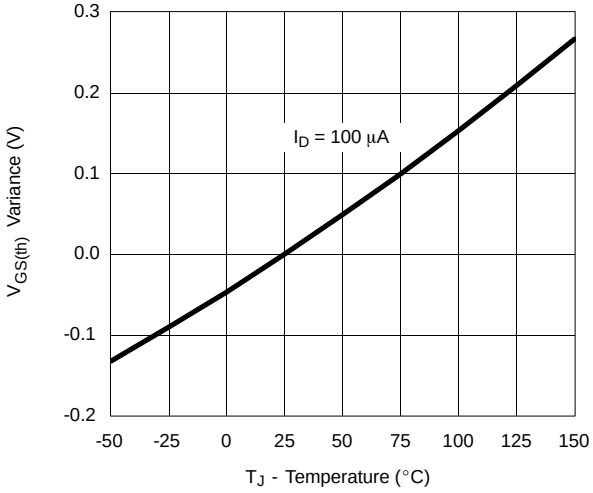
Source-Drain Diode Forward Voltage



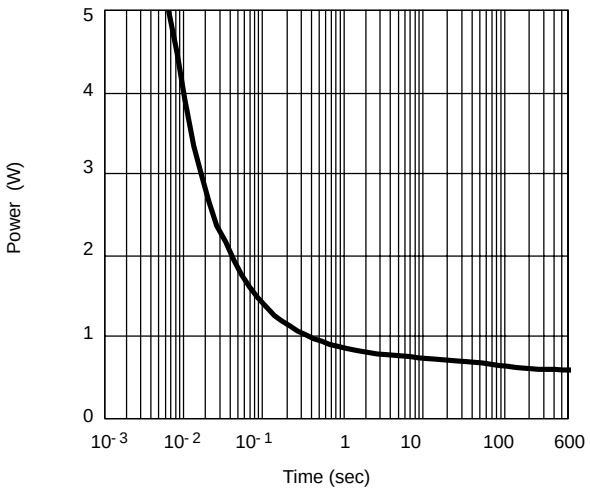
On-Resistance vs. Gate-to-Source Voltage



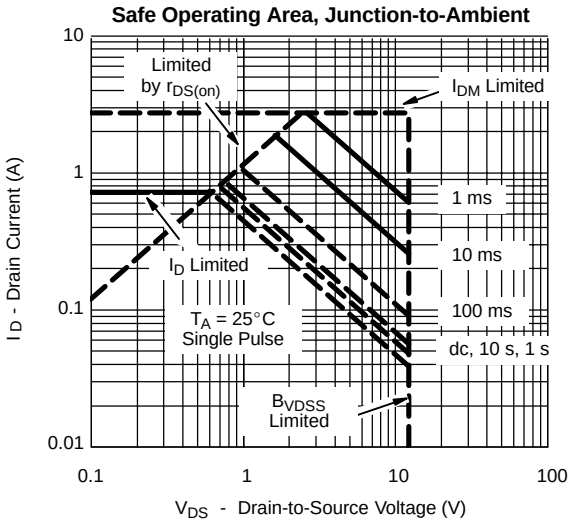
Threshold Voltage



Single Pulse Power

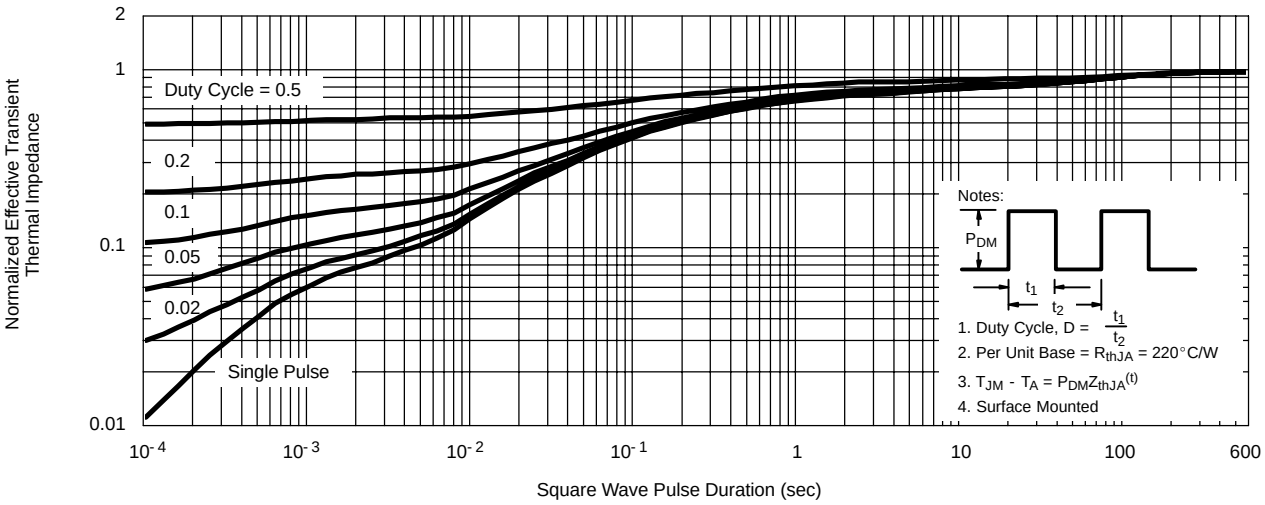


Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

